



### NPN SURFACE MOUNT TRANSISTOR

## **Features**

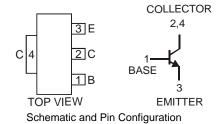
- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DCX53)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

## **Mechanical Data**

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



SOT89-3L



# **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	Ic	1	A
Peak Pulse Current	I <sub>CM</sub>	1.5	A

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	1	W
Operating and Storage Temperature Range	$T_j$ , $T_{STG}$	-55 to +150	°C
Thermal Resistance, Junction to Ambient Air (Note 3) @T <sub>A</sub> = 25°C	$R_{ hetaJA}$	125	°C/W

## Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (No	OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Vo	Collector-Base Breakdown Voltage		100			V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	80	_		V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage		V <sub>(BR)EBO</sub>	5.0	_		V	$I_E = 10\mu A, I_C = 0$
Collector-Base Cutoff Current		I <sub>CBO</sub>	l		0.1 20	μА	$V_{CB} = 30V, I_E = 0$ $V_{CB} = 30V, I_E = 0, T_A = 150$ °C
Emitter-Base Cutoff Current		I <sub>EBO</sub>		_	100	nA	$V_{EB} = 5.0V, I_C = 0$
ON CHARACTERISTICS (Note 4)					_		
DC Current Gain	DCX56, DCX56-16	h <sub>FE</sub>	63		_		$I_C = 5.0 \text{mA}, V_{CE} = 2.0 \text{V}$
	DCX36, DCX36-16		40				$I_C = 500 \text{mA}, V_{CE} = 2.0 \text{V}$
	DCX56		63	_	250		$I_C = 150 \text{mA}, V_{CE} = 2.0 \text{V}$
	DCX56-16		100	_	250	_	$I_C = 150 \text{mA}, V_{CE} = 2.0 \text{V}$
Collector-Emitter Saturation Voltage		V <sub>CE(SAT)</sub>	_	_	0.5	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Turn-On Voltage		V <sub>BE(ON)</sub>	_	_	1.0	V	I <sub>C</sub> = 500mA, V <sub>CE</sub> = 2.0V
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product		f <sub>T</sub>		200		MHz	$I_C = 50 \text{mA}, V_{CE} = 5 \text{V},$ f = 100MHz
Output Capacitance		$C_{obo}$		_	15	pF	$V_{CB} = 10V, I_E = 0, f = 1MHz$

No purposefully added lead. Notes:

- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Measured under pulsed conditions. Pulse width =  $300\mu$ s. Duty cycle  $\leq$ 2%.



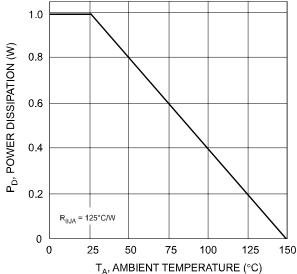
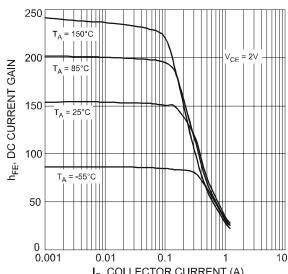


Fig. 1 Power Dissipation vs. Ambient Temperature



 ${\rm I_C}$ , COLLECTOR CURRENT (A) Fig. 3 Typical DC Current Gain vs. Collector Current

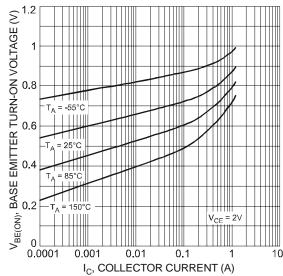
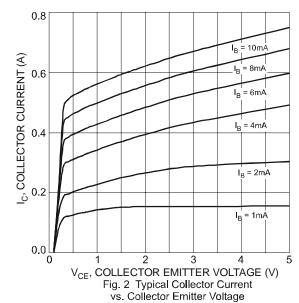


Fig. 5 Typical Base Emitter Turn-On Voltage vs. Collector Current



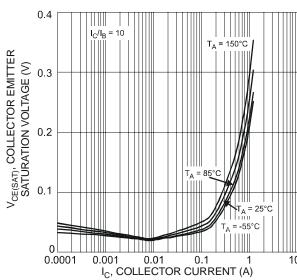


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

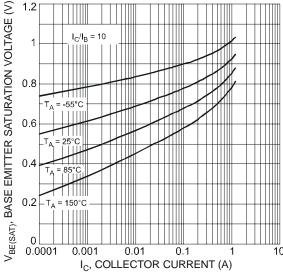
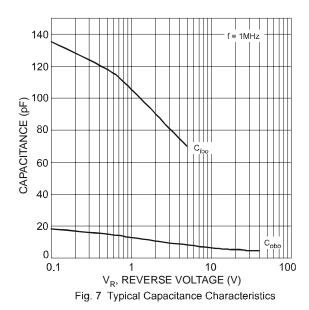
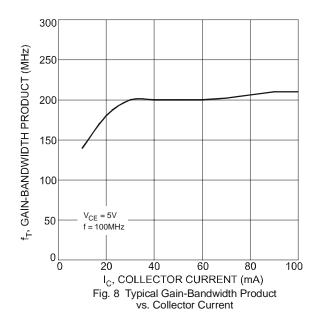


Fig. 6 Typical Base Emitter Saturation Voltage vs. Collector Current





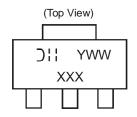


# **Ordering Information (Note 5)**

Device	Packaging	Shipping
DCX56-13	SOT89-3L	2500/Tape & Reel
DCX56-16-13	SOT89-3L	2500/Tape & Reel

5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf. Notes:

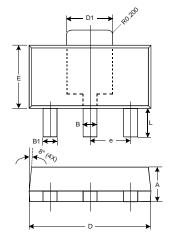
# **Marking Information**

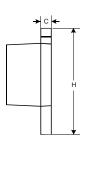


XXX = Product Type Marking Code ex. N18 = DCX56 N18-16 = DCX56-16

☐ = Manufacturer's code marking YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

# **Package Outline Dimensions**

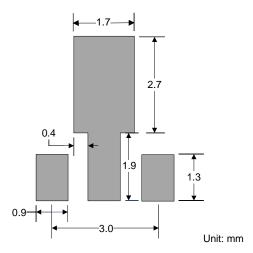




SOT89-3L				
Dim	Min	Max	Тур	
Α	1.40	1.60	1.50	
В	0.45	0.55	0.50	
B1	0.37	0.47	0.42	
С	0.35	0.43	0.38	
D	4.40	4.60	4.50	
D1	1.50	1.70	1.60	
Е	2.40	2.60	2.50	
е	_	1	1.50	
Н	3.95	4.25	4.10	
L	0.90	1.20	1.05	
All Dimensions in mm				



# **Suggested Pad Layout**



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